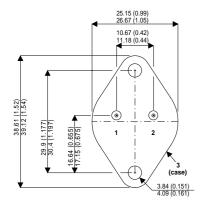


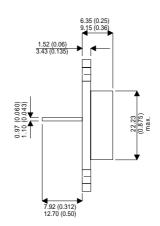


SILICON PLANAR EPITAXIAL NPN POWER SWITCHING TRANSISTOR

MECHANICAL DATA

Dimensions in mm (inches)





FEATURES

- CECC SCREENING OPTIONS
- SPACE QUALITY LEVELS OPTIONS
- JAN LEVEL SCREENING OPTIONS

TO-3 PACKAGE (TO-204AA)

Underside View

PAD 1 – Base PAD 2 – Emitter PAD 3 – Collector

APPLICATIONS:

The BUY24 is a silicon planar epitaxial NPN transistor in a TO-3 (TO-204AA) metal case. It is suitable for switching applications up to 5A.

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

V_{CBO}	Collector - Base Voltage (I _E = 0)	120V
V_{CEO}	Collector - Emitter Voltage (I _B = 0)	60V
V_{EBO}	Emitter - Base Voltage (I _C = 0)	6V
$I_{\mathbb{C}}$	Collector Current	5A
P _{tot}	Total Power Dissipation at T _{case} < 75°C	15W
R $_{ m JC}$	Thermal Resistance Junction To Case	5°C/W
T_{STG}	Storage Temperature	-55 to +150°C
T_J	Junction Temperature	150°C

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ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter		Test Conditions		Min.	Тур.	Max.	Unit
I _{CBO}	Collector-Cutoff Current	V _{CB} =60V	I _E =0			10	μΑ
			T _C =125°C			1	mA
V _{(BR)CEO*}	Collector-Emitter Breakdown Voltage	I _C =50mA	I _B =0	60			
V _{(BR)CBO*}	Collector-Base Breakdown Voltage	I _C =1mA	I _E =0	120			
V _{(BR)EBO*}	Emitter-Base Breakdown Voltage	I _E =1mA	I _C =0	6			
V _{CE (sat)*}	Collector-Emitter Saturation Voltage	I _C =2A	I _B =0.2A		0.15	0.6	V
		I _C =5A	I _B =0.5A		0.4	1.0	
V _{BE(sat)*}	Base-Emitter Saturation Voltage	I _C =2A	I _B =0.2A		0.9	1.2	
		I _C =5A	I _B =0.5A		1.1	1.3	
h_{FE^*}	DC Current Gain	I _C =0.5A	V _{CE} =2V	45	100		
		I _C =2A	$V_{CE}=2V$	40	85		
		I _C =5A	V _{CE} =2V		40		
f _T	Transition Frequency	I _C =0.5A	V _{CE} =5V		100		MHz
C _{CBO}	Collector-Base Capacitance	I _E =0	V _{CB} =10V		35	80	рF
t _{on}	Turn-on Time	I _C =5A	I _{B1} =0.5A		150	350	no
t _{off}	Turn-off Time	I _C =5A	$I_{B1} = I_{B2} = 0.5A$		350	650	ns
h _{fe}	Small Signal Current Gain	I _C =0.5A	V _{CE} =5V	2.5	5		
		f=20MHz					

^{*} Pulsed: Pulse Duration = 300µs, duty cycle = 1.0%

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